

Some of the electrical and thermoelectrical properties for CdO thin films prepared using pulsed laser deposition method

Farah G. Khalid¹, A. S. Ibraheem², Makram A. Fakhri^{3,4,a)}, and Najwan H. Numan³

ABSTRACT

A pulsed Nd:YAG laser was used for the ablation of CdO target in the presence of low oxygen pressure as reactive atmosphere in order to prepare CdO TCO's films. The electrical properties of these films have been investigated at different oxygen pressures (20-100) mbar reaching to the optimum oxygen pressure at which the device could be prepared. Minimum obtained electrical resistivity found to be $7.56 \times 10^{-3} \Omega \cdot \text{cm}$ at 80 mbar of oxygen ambient without using post-deposition heat treatment. The thermoelectrical properties revealed the formation of n-type semiconducting material.